

Silicon NPN Power Transistors

S2055AF

DESCRIPTION

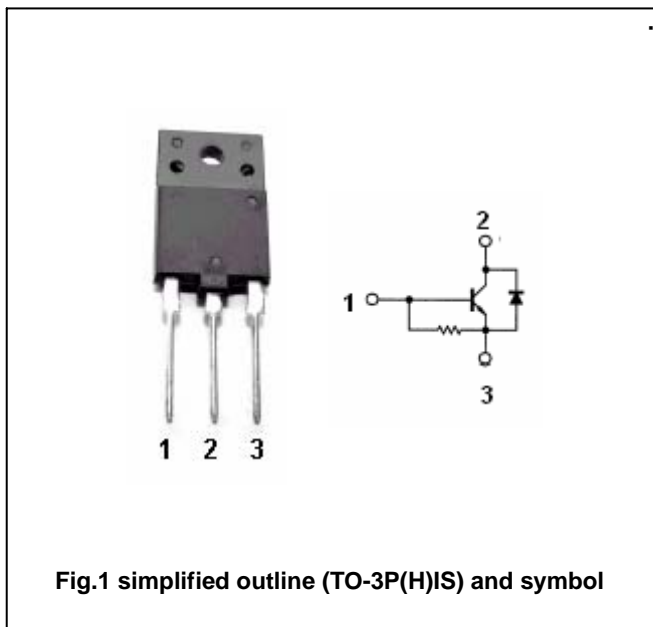
- With TO-3P(H)IS package
- High voltage ;high speed
- Built-in damper diode

APPLICATIONS

- Horizontal deflection for color TV

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1500	V
$V_{CEO}$	Collector-emitter voltage	Open base	700	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		8	A
$I_{CM}$	Collector current-peak		15	A
$P_C$	Collector power dissipation	$T_C=25$	50	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	2.5	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	700			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2.0A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =2.0A			1.3	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1500V; V <sub>BE</sub> =0 T <sub>C</sub> =125			1 2	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			300	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V; f=5MHz		7		MHz

Switching times inductive load

t <sub>s</sub>	Storage time	I <sub>C</sub> =4.5A ; h <sub>FE</sub> =2.5; V <sub>CC</sub> =140V L <sub>C</sub> =0.9mH; L <sub>B</sub> =3 μ H		7		μ s
t <sub>f</sub>	Fall time			0.55		μ s

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PACKAGE OUTLINE

